## NSN 5962-01-375-0370

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Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
End Application:
Eo lorops
Features Provided:
Electrostatic sensitive and ultraviolet erasable and monolithic and programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Input Circuit Pattern:
22 input
Criticality Code Justification:
Feat
Current Rating Per Characteristic:
5.50 milliamperes forward current, nonrepetitive, peak total value microamperes
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit programmed; microcircuits, memory, digital, cmos uv erasable, programmable array logic, monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
25.00 nanoseconds propagation delay
Memory Device Type:
Pal
Special Features:
Electrostatic discharge senstive; altered item, device to be programmed is pn 5962-8753901la, cage 67268, filename 1058-u8.Jed sumcheck
9d2d; nha pn 1372ae1058 cage 72314
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:
N/a
Unit Of Measure:
<del></del>

Yes - demil/mli

Demilitarization:

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